

**AMENDMENTS TO THE CLAIMS:**

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

**LISTING OF CLAIMS:**

1. (Currently Amended) A semiconductor device comprising:  
first and second electrodes having layers containing copper as main components;  
a semiconductor element arranged between said first and second electrodes and electrically connected to said first and second electrodes; and  
a glass sealing member which seals said first electrode, said semiconductor element, and said second electrode,  
wherein, in the first and second electrodes, ratios of the layers containing copper as main components are ~~not less~~ more than 20 wt%.
2. (Original) The semiconductor device according to claim 1,  
wherein said first and second electrodes are constituted by Dumet wires.
3. (Original) The semiconductor device according to claim 1,  
wherein said semiconductor element is a diode.
4. (Original) The semiconductor device according to claim 1,  
wherein said semiconductor element is a Schottky barrier diode.
5. (Currently Amended) The semiconductor device according to claim 1,  
wherein the semiconductor element has a metal electrode, and  
wherein a sealing temperature of said glass sealing member is 630°C or less and is a temperature at which silicification of said metal electrode of the semiconductor element is not enhanced.

6. (Original) The semiconductor device according to claim 1,  
wherein a glass softening point of said glass sealing member is 560°C or  
less.
7. (Canceled)
8. (Canceled)
9. (Original) The semiconductor device according to claim 1,  
wherein the semiconductor element has a bump electrode, and  
wherein the thickness of said layers containing copper as main  
components are larger than said thickness of said bump electrode.
10. (Currently Amended) The semiconductor device according to claim 1,  
wherein, in said first and second electrodes, ratios of said layers  
containing copper as main components ~~fall within the range of 20 to 25 wt%~~ are  
more than 20 wt% and equal to or less than 25 wt%.
11. (Original) The semiconductor device according to claim 1,  
wherein, in said first and second electrodes, ratios of said layers  
containing copper as main components fall within the range of 21 to 24 wt%.
12. (Original) The semiconductor device according to claim 1,  
wherein said first and second embodiments have core portions and said  
layers containing copper as main components, said layers being formed on the  
outer peripheries of said core portions.
13. (Original) The semiconductor device according to claim 12,

wherein said core portions of said first and second electrodes comprise a nickel-containing alloy.

14. (Original) The semiconductor device according to claim 12,  
wherein said core portions of said first and second electrodes are  
comprised of a nickel-containing alloy having a nickel content of 45 wt% or less.

15. (Original) The semiconductor device according to claim 12,  
wherein said core portions of said first and second electrodes are  
comprised of a nickel-containing alloy having a nickel content falling within the  
range of 41 to 43 wt%.

16. (Original) The semiconductor device according to claim 12,  
wherein said core portions of said first and second electrodes are  
comprised of an alloy containing iron and nickel as main components.

17. (Currently Amended) The semiconductor device according to claim 12,  
wherein said first and second electrodes have copper oxide layers formed  
on the outer peripheries of said layers containing copper as main components,  
the copper oxide layers contacting with said glass sealing member.

18. (Original) The semiconductor device according to claim 17,  
wherein the thickness of the copper oxide layers are 1.5  $\mu\text{m}$  or less.

19. (Original) The semiconductor device according to claim 1,  
wherein said semiconductor element comprises by a Schottky barrier  
diode having:

a semiconductor substrate;

an epitaxial layer formed on the semiconductor substrate; and

a metal electrode formed on the epitaxial layer.

20. (Original) The semiconductor device according to claim 19,  
wherein said metal electrode has a tungsten film.
21. (New) The semiconductor device according to claim 1,  
wherein the semiconductor element has a metal electrode, and  
wherein a sealing temperature of said glass sealing member is 620°C or  
less and is a temperature at which silicification of said metal electrode of the  
semiconductor element is not enhanced.